

LD83O6S-A/B/C

AlGaAs Laser Diode

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◆ OVERVIEW

LD83O6S-A/B/C is a MOCVD grown 830nm band AlGaAs laser diode with quantum well structure. It's an attractive light source, with a typical light output power of 100mW for industrial optical module and sensor applications.

◆ APPLICATION

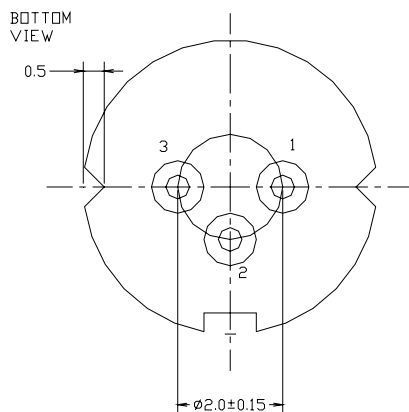
- Optical Sensor
- Industrial Optical Module

◆ FEATURES

- Visible Light Output : $\lambda_p = 830 \text{ nm}$
- Optical Power Output : 100mW CW
- Package Type : TO-18 (5.6mm ϕ)
- Built-in Photo Diode for Monitoring Laser Diode

◆ ELECTRICAL CONNECTION

Bottom View



Pin Configuration

A	LD cathode, PD anode (Fig. 1)
B	LD , PD anode (Fig. 2)
C	LD anode, PD cathode (Fig. 3)

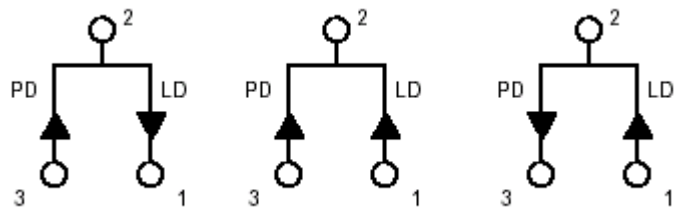


Fig. 1

LD83O6SA

Fig. 2

LD83O6SB

Fig. 3

LD83O6SC

◆ ABSOLUTE MAXIMUM RATING at Tc=25°C

Items	Symbols	Values	Unit
Optical Output Power	P	100	mW
Laser Diode Reverse Voltage	V	2	V
Photo Diode Reverse Voltage	V	30	V
Operating Temperature	Topr	-10 ~ +60	°C
Storage Temperature	Tstg	-40 ~ +85	°C

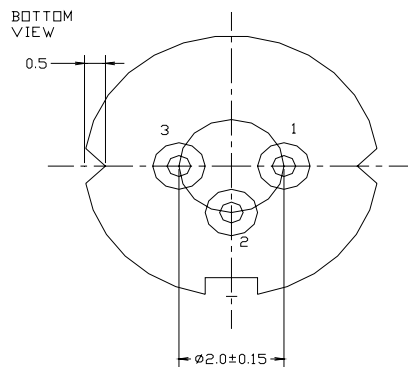
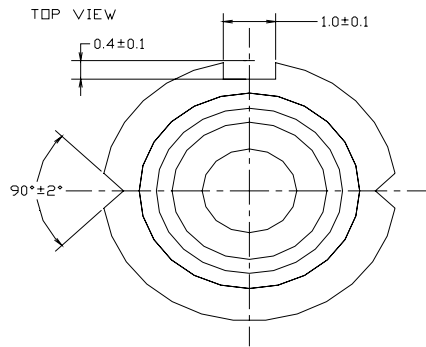
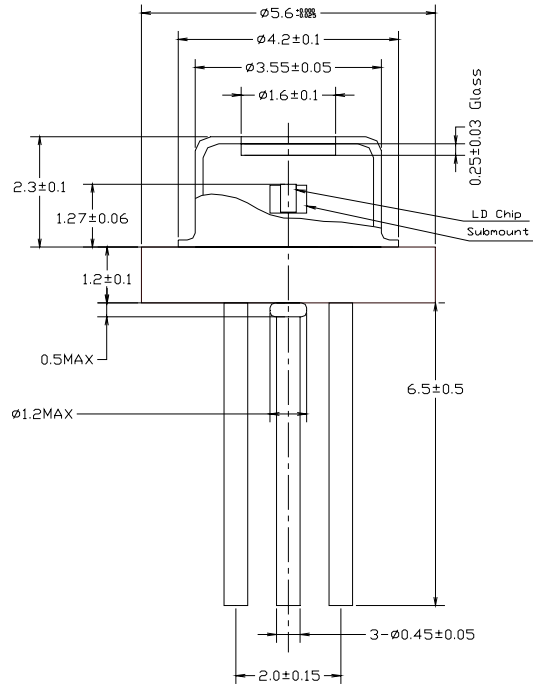
◆ ELECTRICAL and OPTICAL CHARACTERISTICS at Tc=25°C

Items	Symbols	Min.	Typ.	Max.	Unit	Condition
Optical Output Power	Po	-	100	-	mW	-
Threshold Current	Ith	-	70	80	mA	-
Operating Current	Iop	210	220	230	mA	Po=100mW
Slope Efficiency	SE	0.5	0.8	1.1	mW/mA	20~100 mW
Operating Voltage	Vop	-	2.2	2.8	V	Po=100mW
Lasing Wavelength	λ_p	820	830	840	nm	Po=100mW
Beam Divergence	θ_{\parallel}	7	10	14	deg	Po=100mW
	θ_{\perp}	15	20	25	deg	Po=100mW
Beam Angle	$\Delta\theta_{\parallel}$	-	-	± 2	deg	Po=100mW
	$\Delta\theta_{\perp}$	-	-	± 3	deg	Po=100mW
Monitor Current	I _m	0.05	0.1	0.4	mA	Po=100mW
Astigmatism	As	-	-	15	μm	
Optical Distance	$\Delta X, \Delta Y, \Delta Z$	-	-	± 60	μm	

NOTICE : LD8306S-A/B/C to be operated on APC

The above product specifications are subject to change without notice.

◆ PACKAGE DIMENSION



◆ PACKING

